

Fig.1A

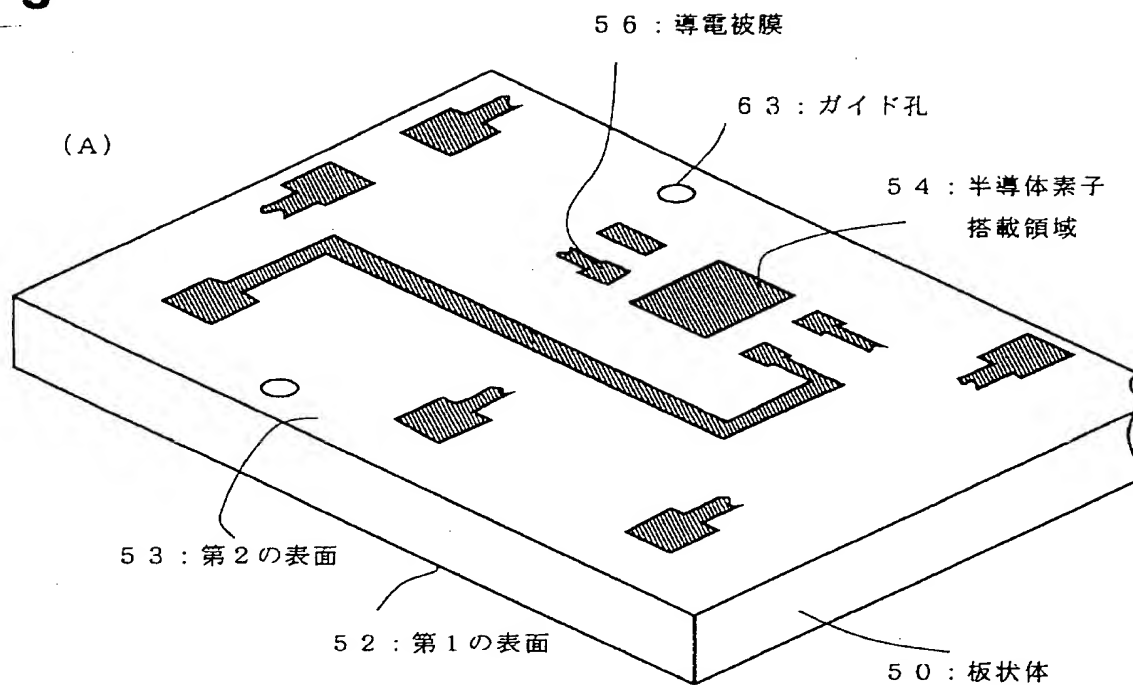


Fig.1B

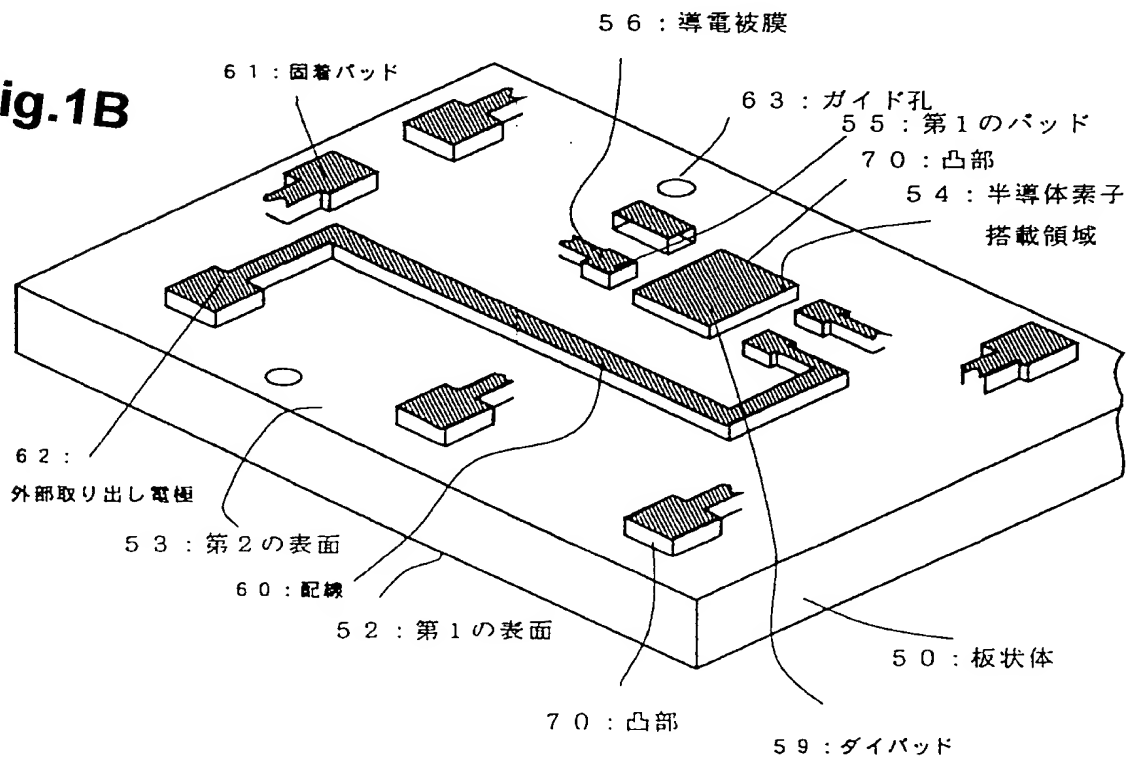
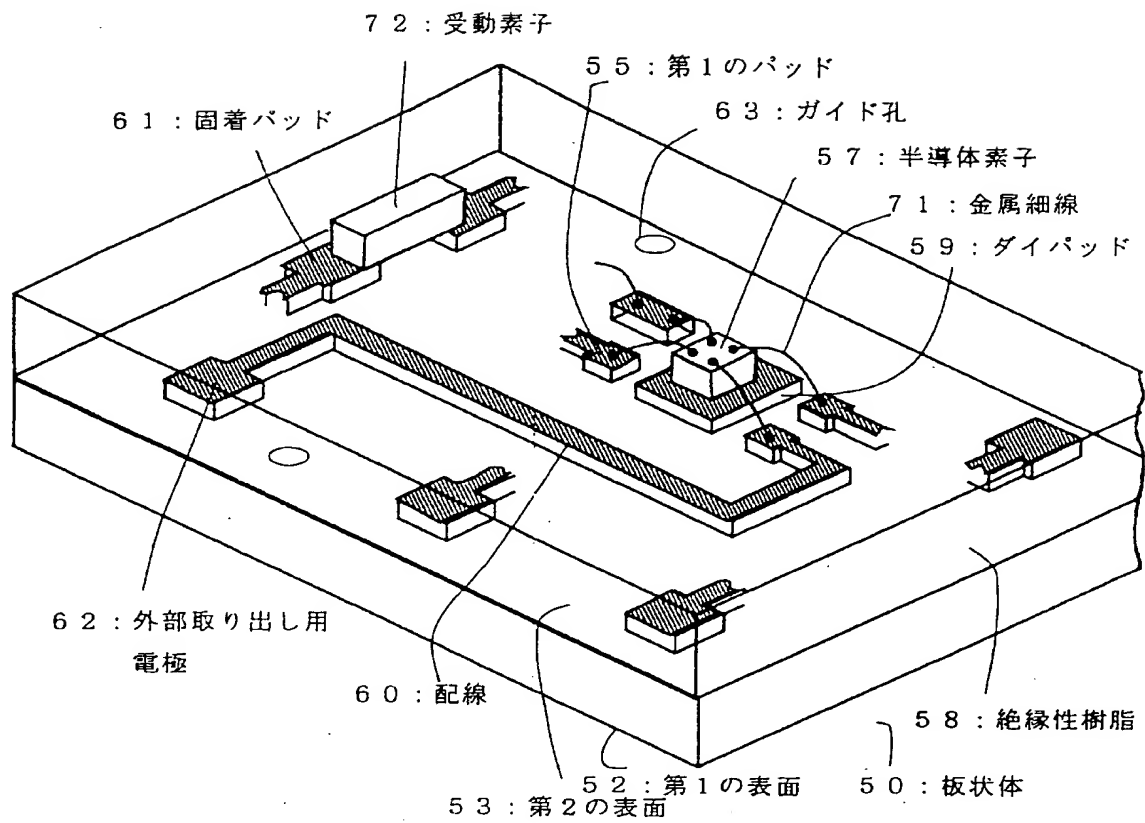
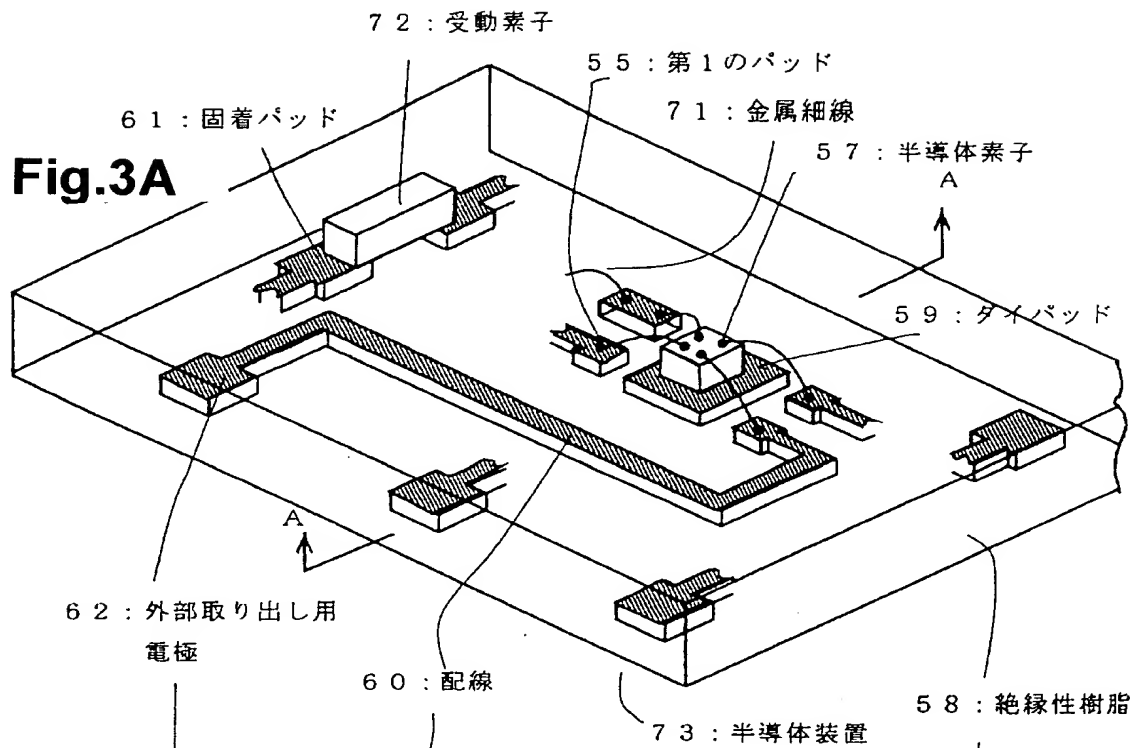


Fig.2





**Fig.3B**

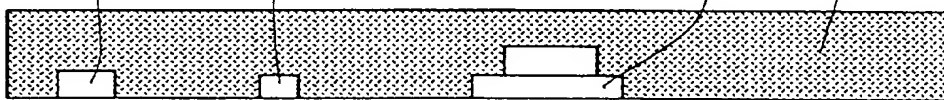


Fig.4

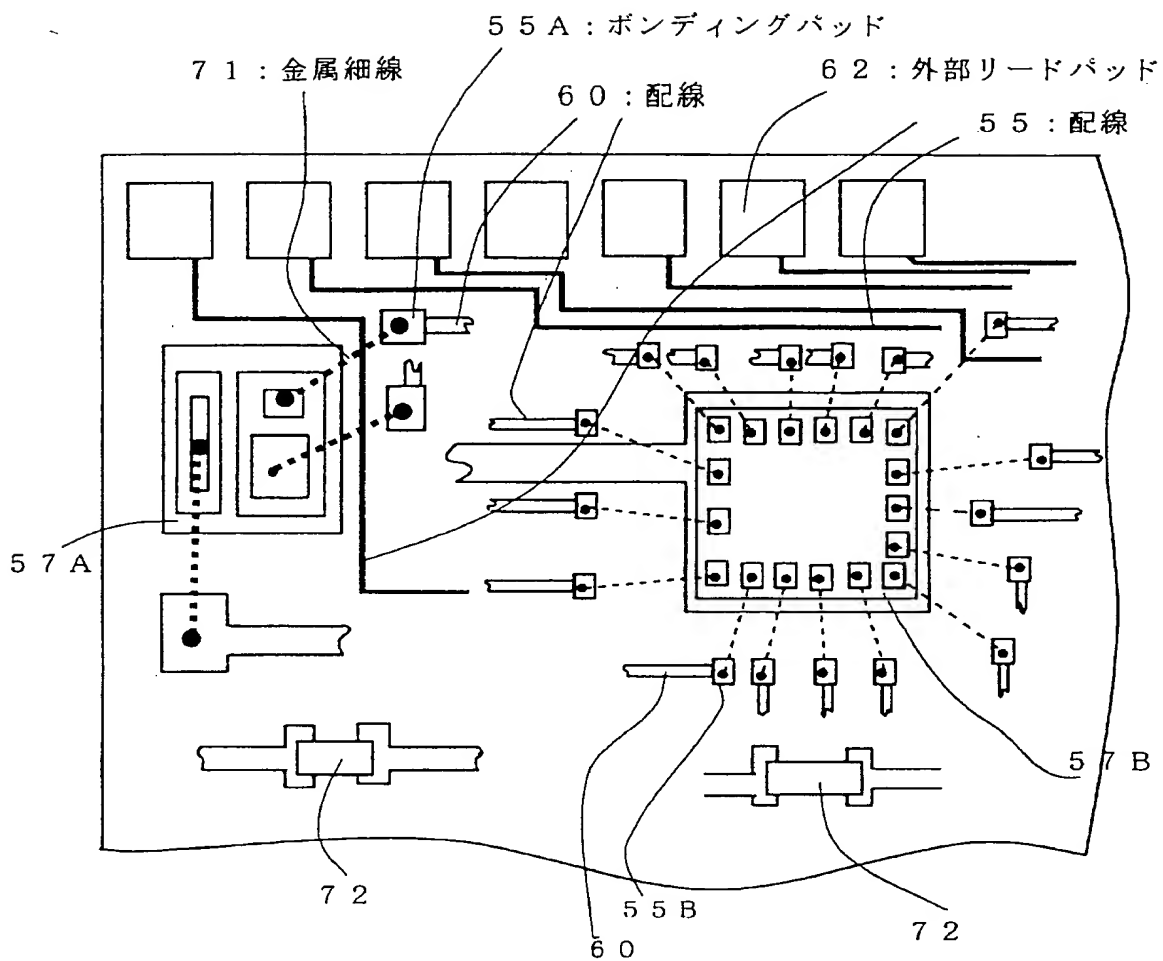
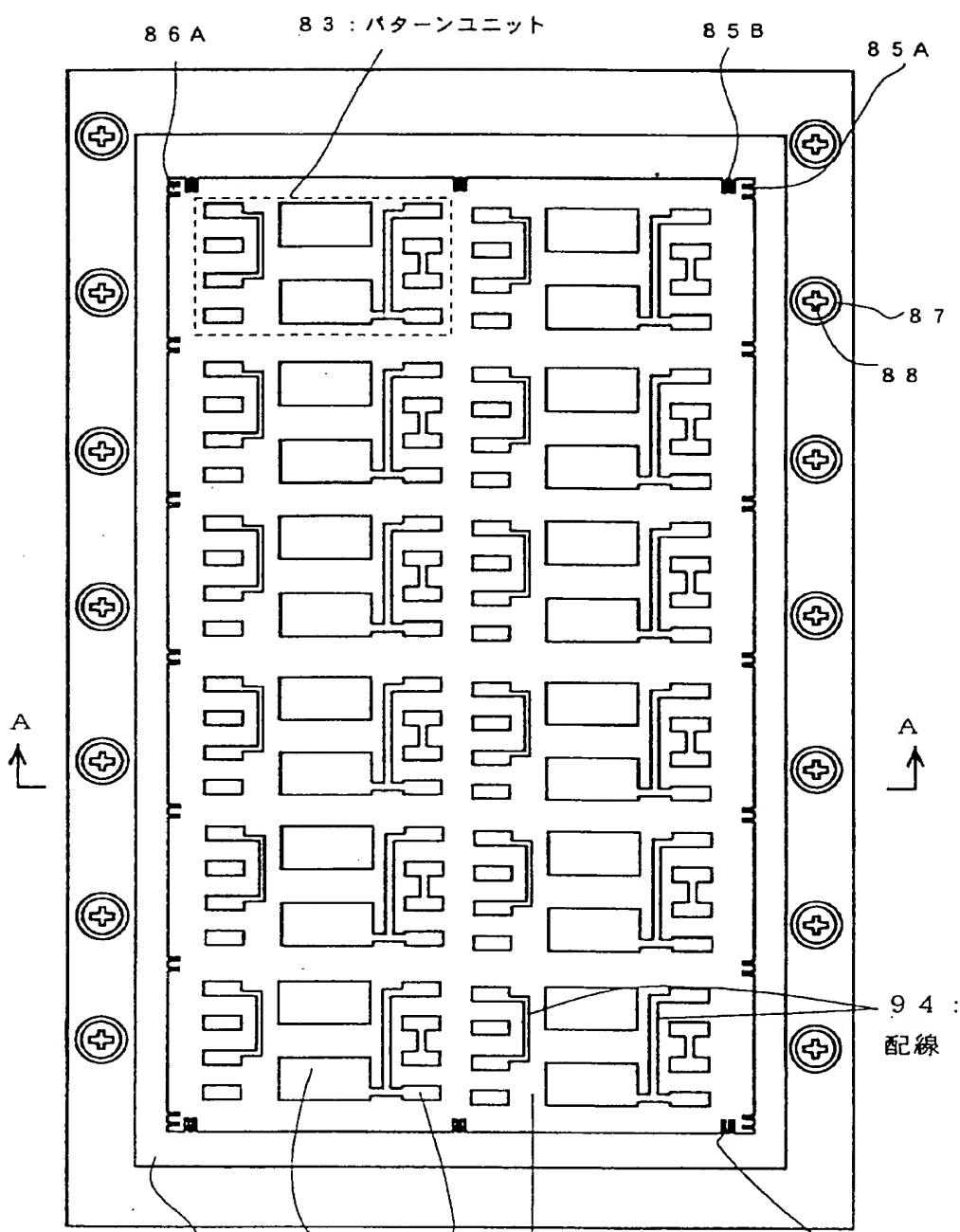


Fig.5A



84 : 金型当接領域

CF

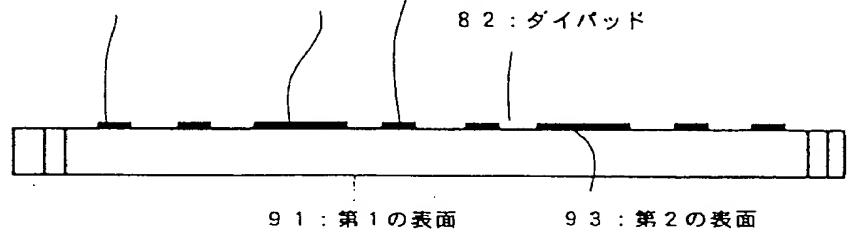
81 : 外部取り出し用電極

82 : ダイパッド

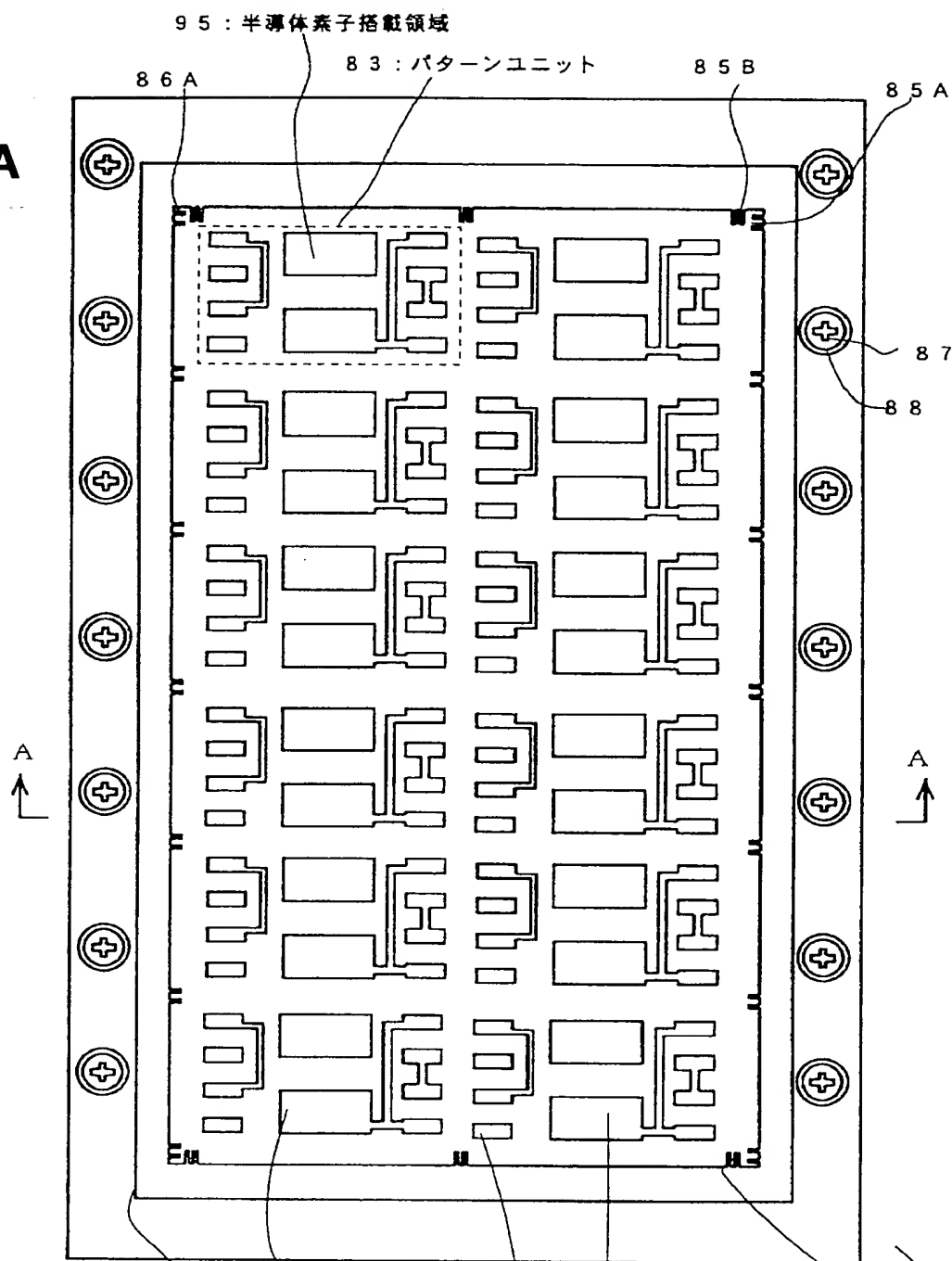
80 : 板状体

86 B

Fig.5B



**Fig.6A**



**Fig.6B**

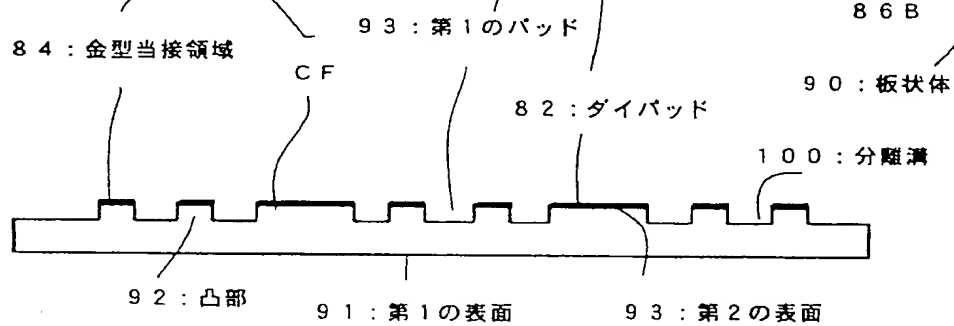


Fig.7A

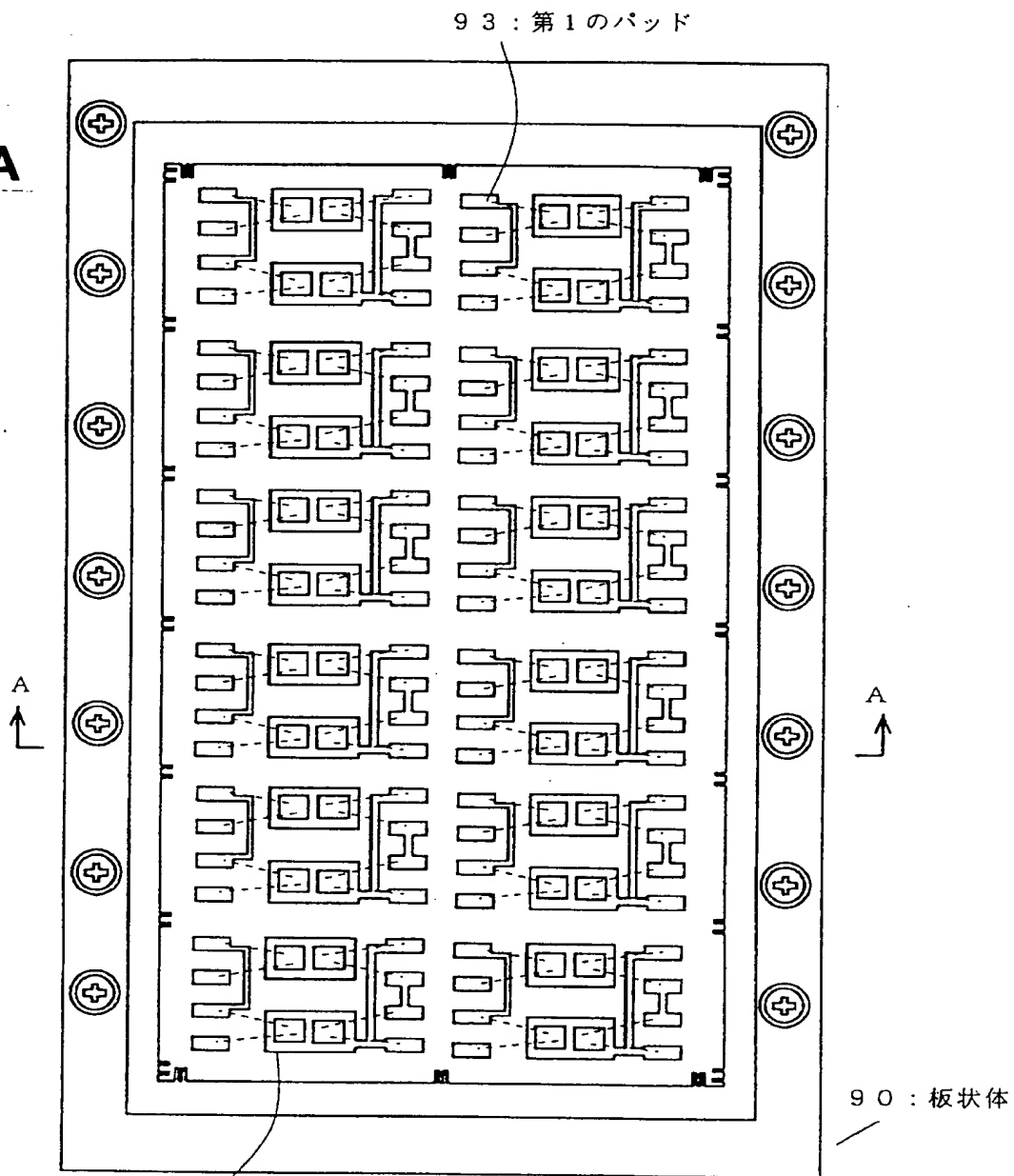
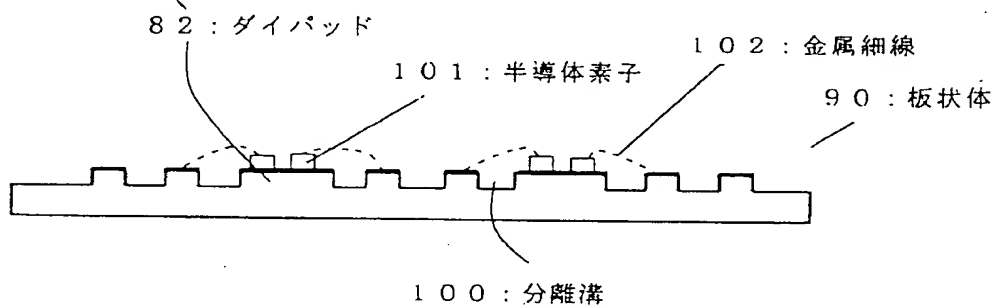
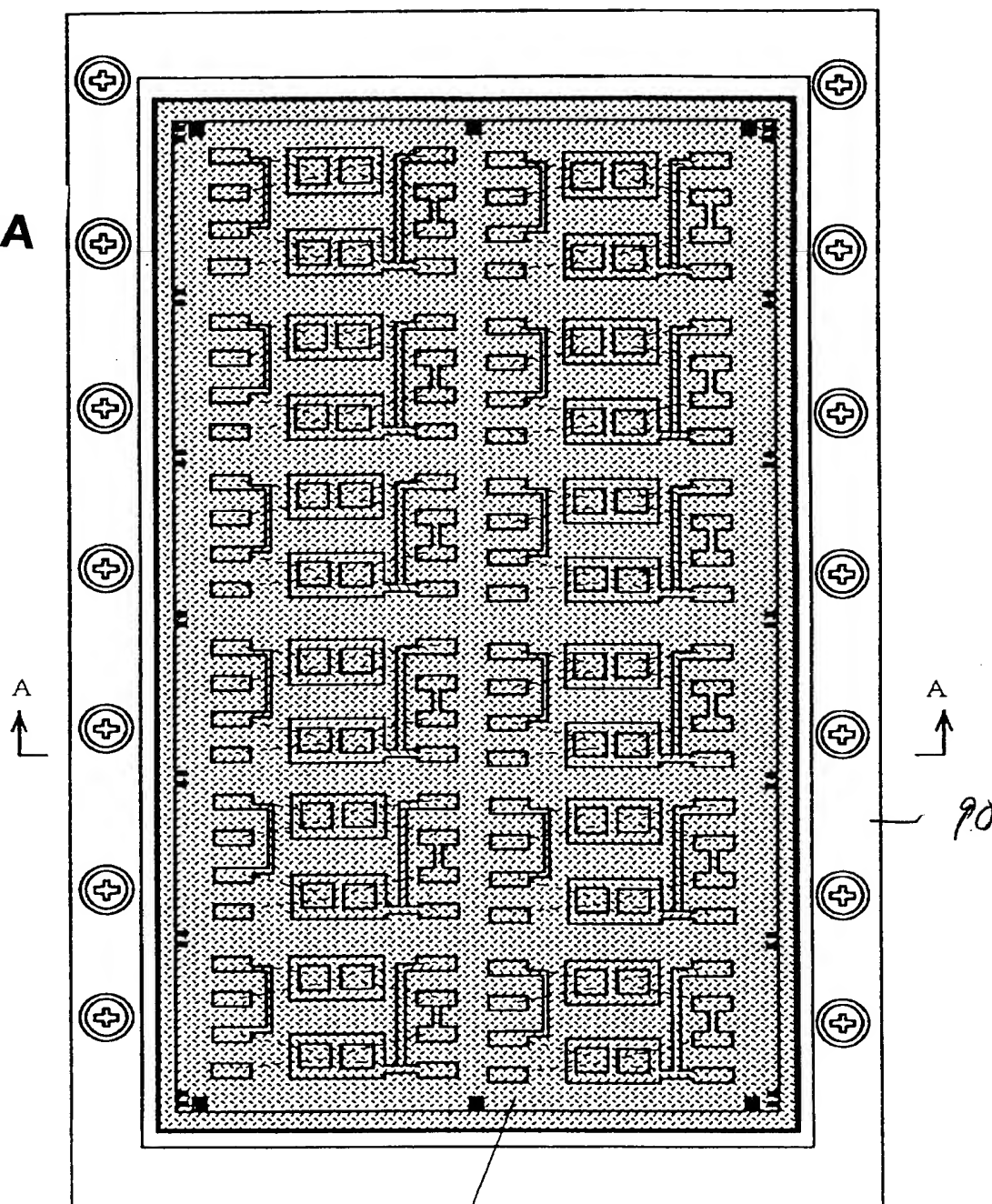


Fig.7B



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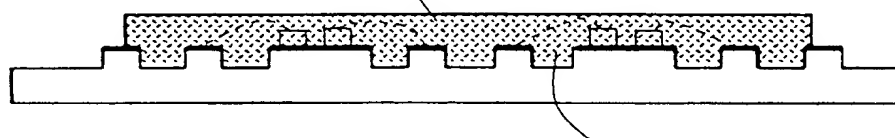
Fig.8A



00678143-100300

103 : 絶縁性樹脂

Fig.8B



100 : 分離溝



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Fig.9A

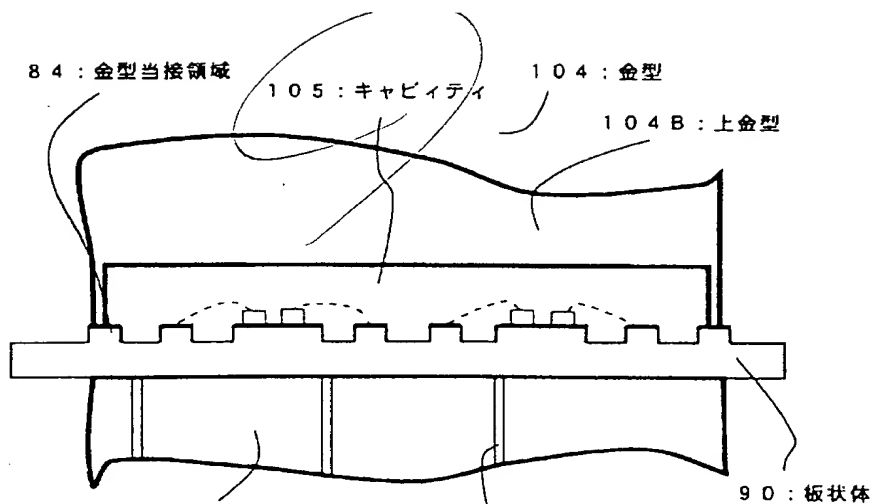


Fig.9B B) 105

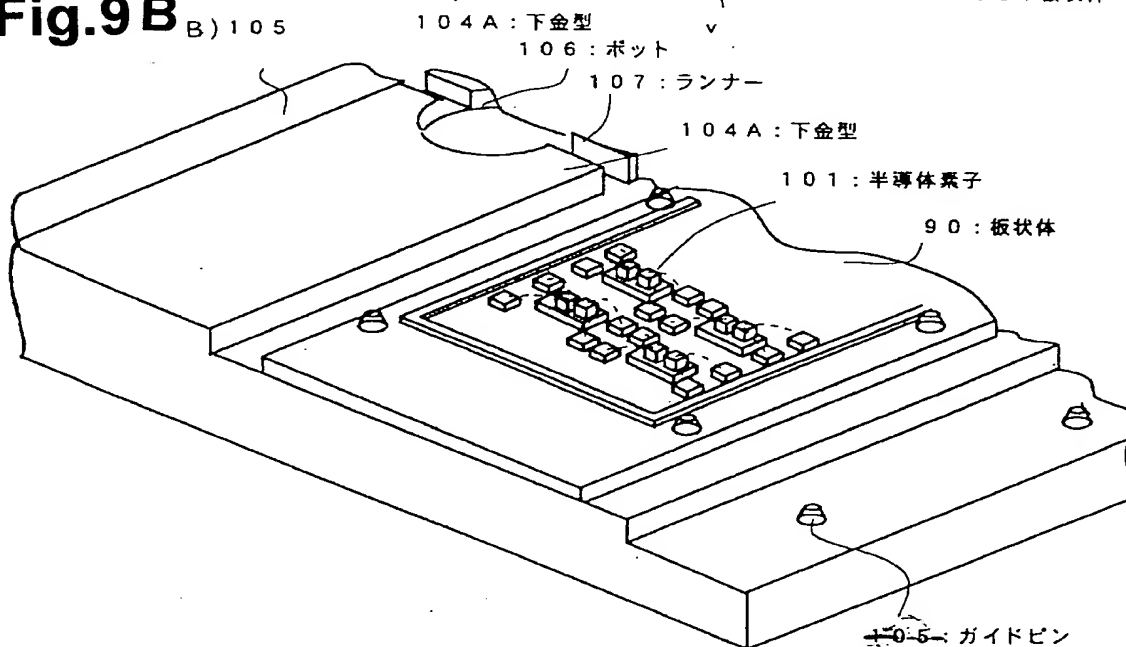
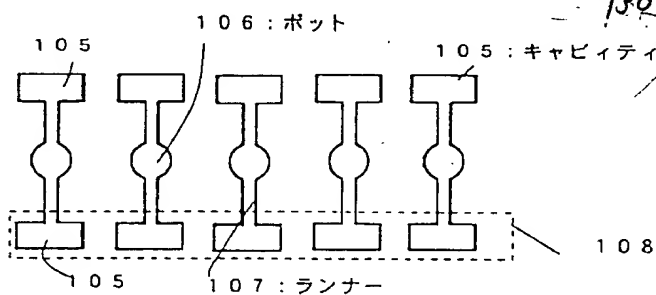


Fig.9C C)



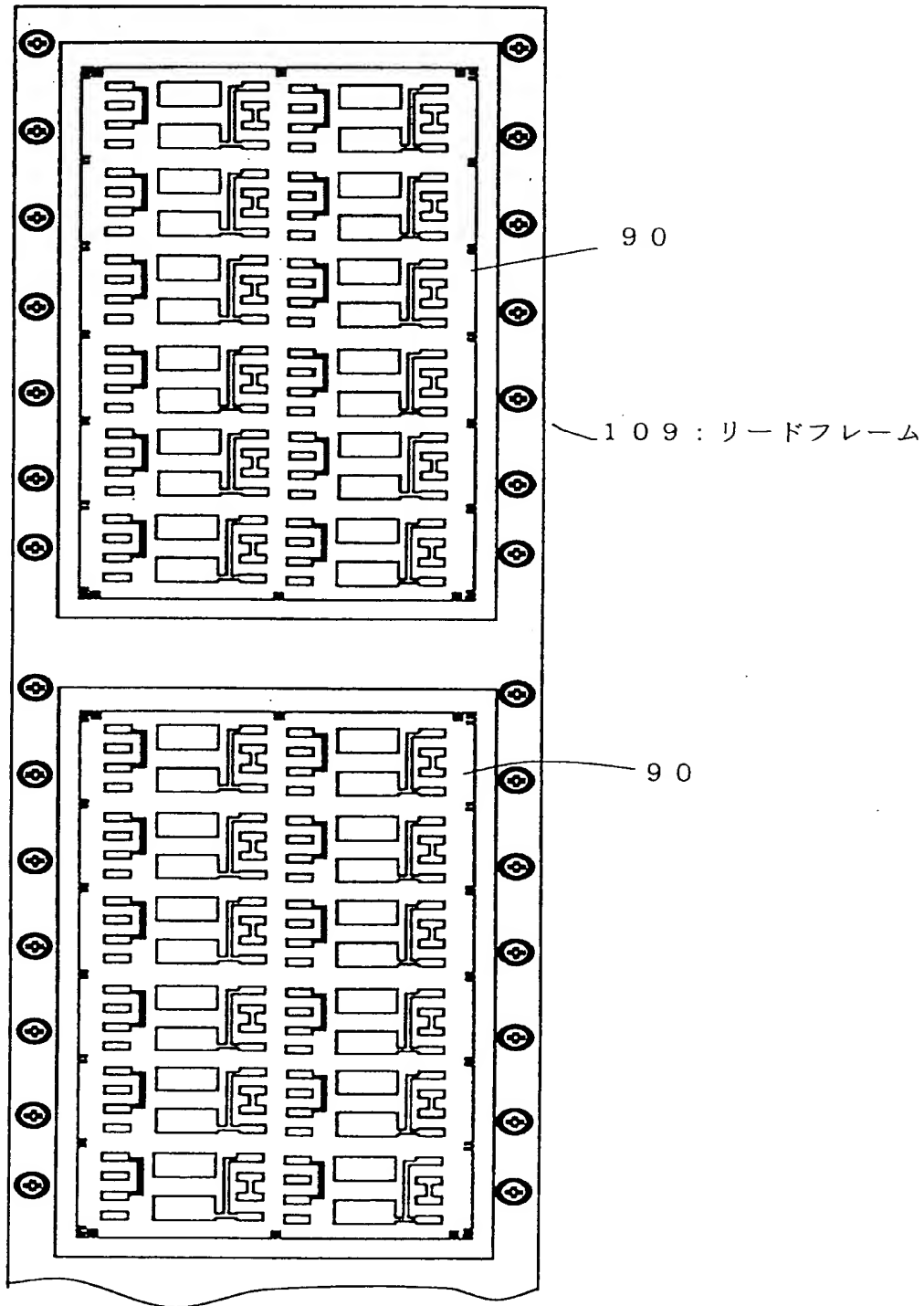
1-7 4

82: アイランド      81: 第1のパッド      100: 分離溝      103: 絶縁性樹脂

Figure 1 is a cross-sectional view of a semiconductor device. It shows a substrate with a thin layer 110 on top. On this layer, there are several rectangular structures 111 (protrusions) and 112 (insulating film). A label 113 points to the entire assembly.

Fig.11

000001-24782960





**Fig.13**

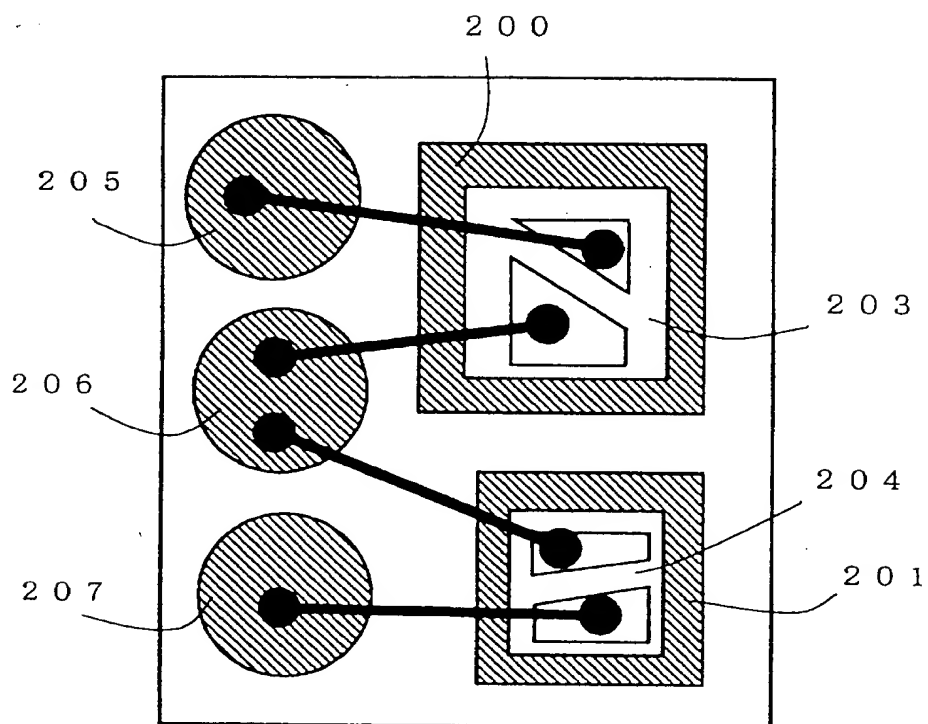
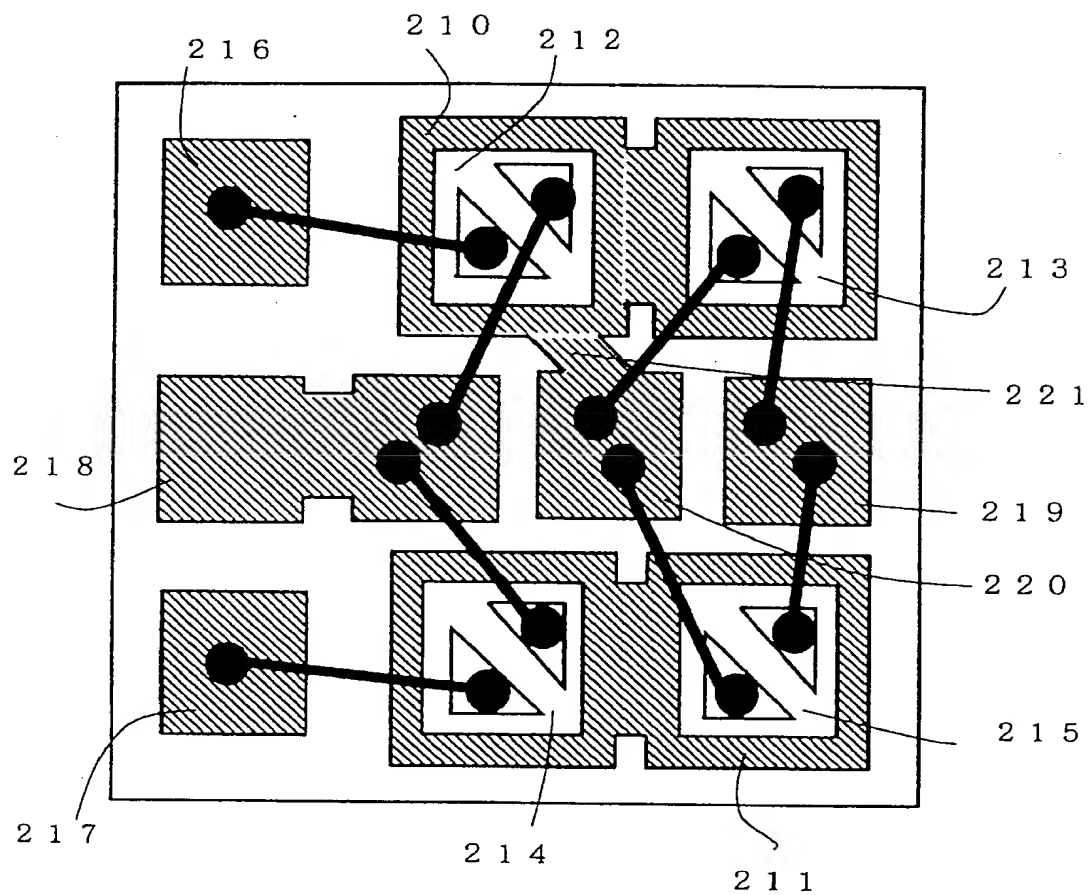


Fig.14



000001-0102-960

Fig.15

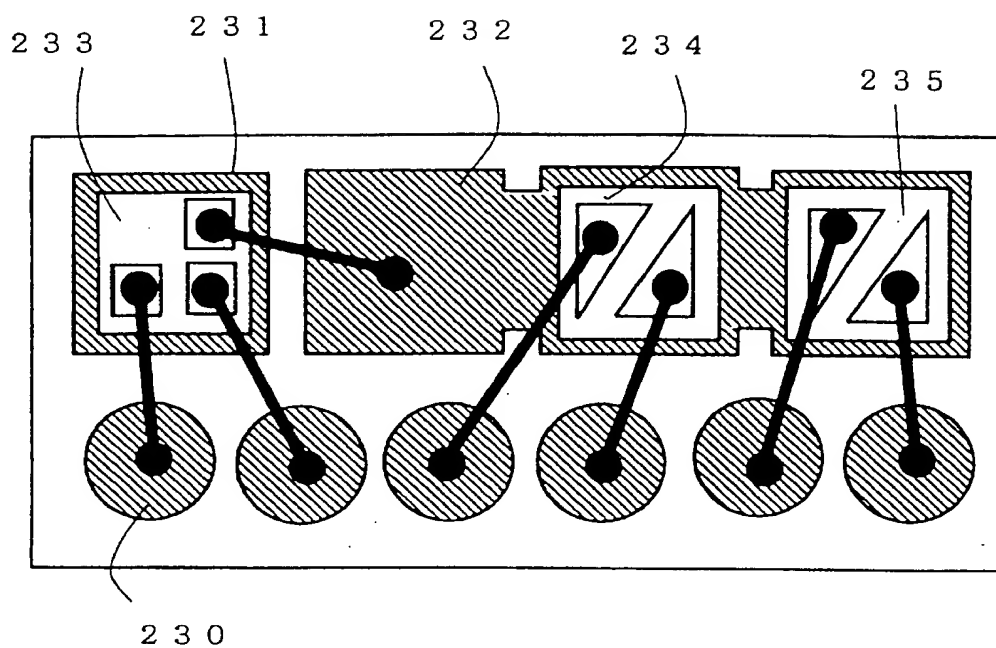
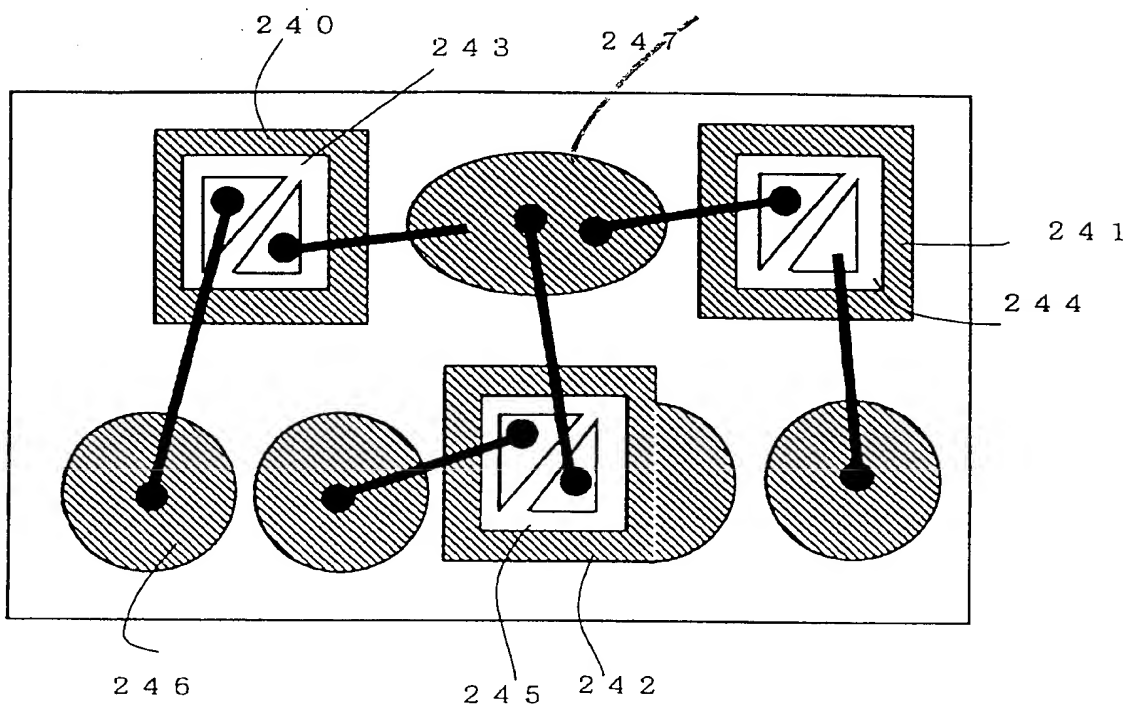
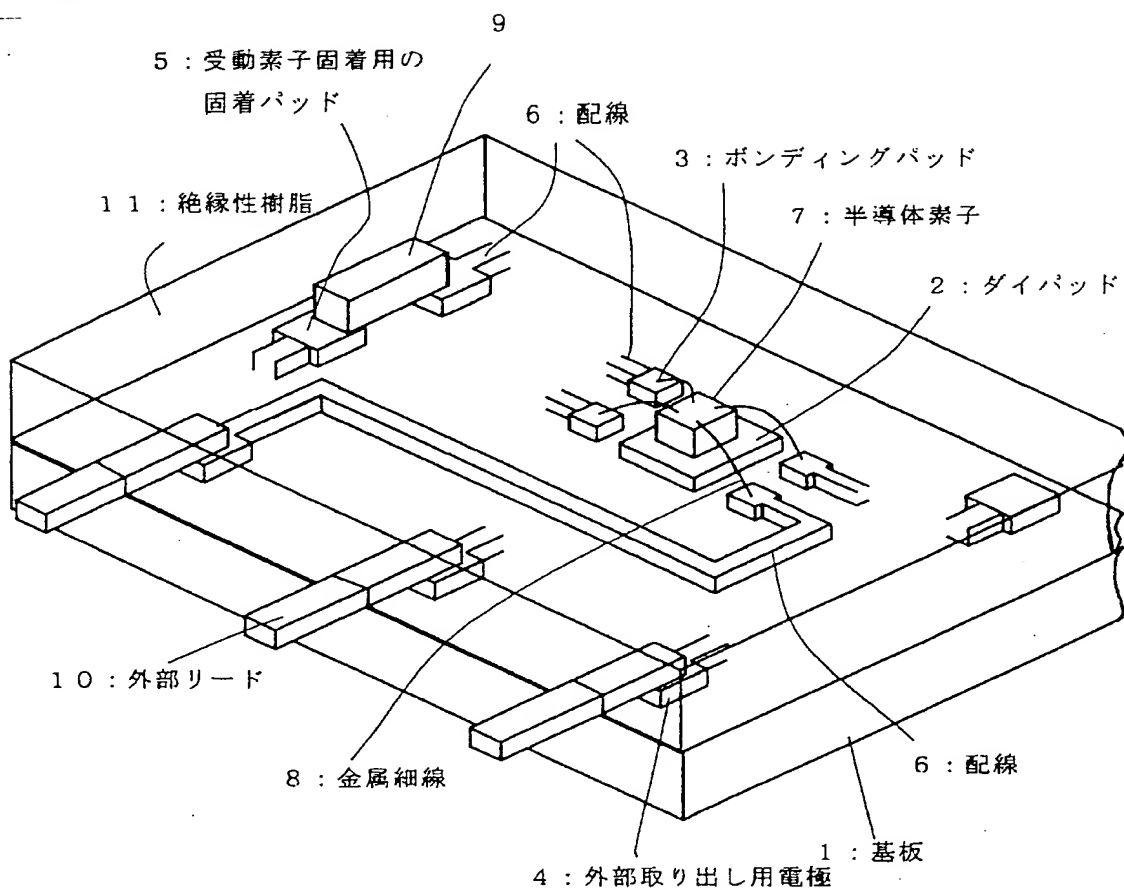


Fig.16



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Fig.17



000001-24152900



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Fig.18A

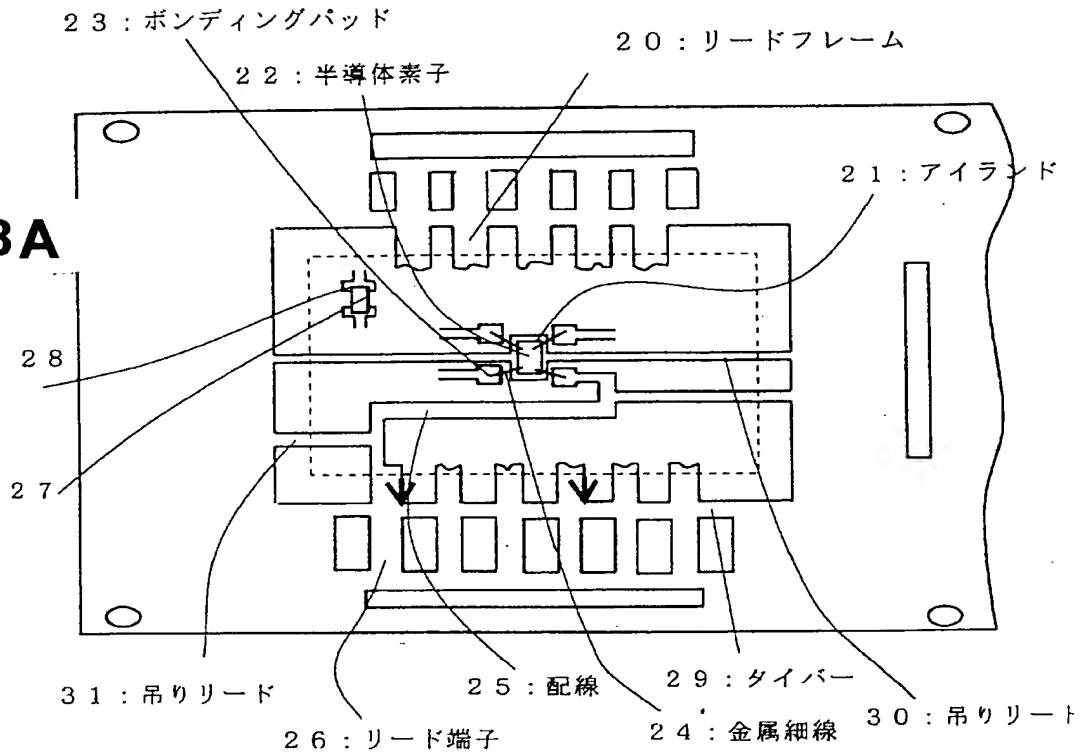


Fig.18B

